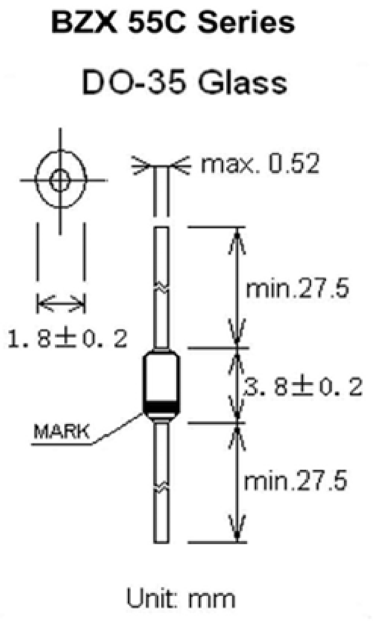
BZX 55C Series

DO-35 玻封稳压二极管

DO-35 Glass Zener Diode



Features

- Low Reverse Leakage
- Low Zener Impedance
- 500mW; Power Dissipation of 500mW
- High Stability and High Reliability

Mechanical Data

- Case: DO-35 Glass Case
- Polarity: Color band denotes cathode end
- Mounting Position: Any

Maximum Ratings & Thermal Characteristics

(Ratings at 25℃ ambient temperature unless otherwise specified.) (TA = 25℃ 除非另有规定)

Parameters	符号 Symbol	数值 Value	单位 Unit
Power Dissipation	Pd	500 [1)]	mW
Operating junction temperature	Tj	175	℃
Storage temperature range	Ts	-55-+175	℃

1) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

Electrical Characteristics

(Ratings at 25℃ ambient temperature unless otherwise specified). (TA = 25℃ 除非另有规定)

TYPE	Zener Voltage			Reverse Carrent		Dynamic Resistance	
	Vz(V)		Test Condition	IR(μA)	Test Condition	rd(Ω)	Test Condition
	Min.	Max.	Iz(mA)	Max.	VR(V)	Max.	Iz(mA)
BZX55C 2V0	1.80	2.15	5.0	100	1.0	85	5.0
BZX55C 2V2	2.08	2.33	5.0	75	1.0	85	5.0
BZX55C 2V4	2.28	2.56	5.0	50	1.0	85	5.0
BZX55C 2V7	2.50	2.90	5.0	10	1.0	85	5.0
BZX55C 3V0	2.80	3.20	5.0	4	1.0	85	5.0
BZX55C 3V3	3.10	3.50	5.0	2	1.0	85	5.0
BZX55C 3V6	3.40	3.80	5.0	2	1.0	85	5.0
BZX55C 3V9	3.70	4.10	5.0	2	1.0	85	5.0
BZX55C 4V3	4.00	4.60	5.0	1	1.0	75	5.0
BZX55C 4V7	4.40	5.00	5.0	0.5	1.0	60	5.0
BZX55C 5V1	4.80	5.40	5.0	0.1	1.0	35	5.0
BZX55C 5V6	5.20	6.00	5.0	0.1	1.0	25	5.0
BZX55C 6V2	5.80	6.60	5.0	0.1	2.0	10	5.0
BZX55C 6V8	6.40	7.20	5.0	0.1	3.0	8	5.0
BZX55C 7V5	7.00	7.90	5.0	0.1	5.0	7	5.0
BZX55C 8V2	7.70	8.70	5.0	0.1	6.2	7	5.0

TYPE	Zener Voltage			Reverse Carrent		Dynamic Resistance	
	Vz(V)		Test Condition	IR(μA)	Test Condition	rd(Ω)	Test Condition
	Min.	Max.	Iz(mA)	Max.	VR(V)	Max.	Iz(mA)
BZX55C 9V1	8.50	9.60	5.0	0.1	6.8	10	5.0
BZX55C 10	9.40	10.60	5.0	0.1	7.5	15	5.0
BZX55C 11	10.40	11.60	5.0	0.1	8.2	20	5.0
BZX55C 12	11.40	12.70	5.0	0.1	9.1	20	5.0
BZX55C 13	12.40	14.10	5.0	0.1	10.0	26	5.0
BZX55C 14	13.30	14.70	5.0	0.1	10.0	26	5.0
BZX55C 15	13.80	15.60	5.0	0.1	11.0	30	5.0
BZX55C 16	15.30	17.10	5.0	0.1	12.0	40	5.0
BZX55C 18	16.80	19.10	5.0	0.1	13.0	50	5.0
BZX55C 20	18.80	21.20	5.0	0.1	15.0	55	5.0
BZX55C 22	20.80	23.30	5.0	0.1	16.0	55	5.0
BZX55C 24	22.80	25.60	5.0	0.1	18.0	80	5.0
BZX55C 27	25.10	28.90	5.0	0.1	20.0	80	5.0
BZX55C 30	28.00	32.00	5.0	0.1	22.0	80	5.0
BZX55C 33	31.00	35.00	5.0	0.1	24.0	80	5.0
BZX55C 36	34.00	38.00	5.0	0.1	27.0	80	5.0
BZX55C 39	37.00	41.00	2.5	0.1	30.0	90	2.5

Notes:

1) Tested with pulses tp = 20 ms.
2) Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case
3) The BZX55-C0V8 is a silicon diode with operation in forward direction. Hence, the index of all parameters should be “F” instead of “Z”. Connect the cathode lead to the negative pole.
4) VF(Max)=1.20V@ IF=100Ma

Breakdown characteristics Tj = constant (pulsed)